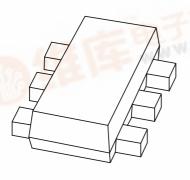
DISCRETE SEMICONDUCTORS

DATA SHEET



BAS70-07V Schottky barrier double diode

Product specification







Schottky barrier double diode

BAS70-07V

FEATURES

- Low forward voltage
- High reverse voltage
- · Low capacitance
- Ultra small plastic SMD package
- Flat leads: excellent coplanarity and improved thermal behaviour.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- · Line termination
- Inverse-polarity protection
- RF applications (e.g. mixing and demodulation).

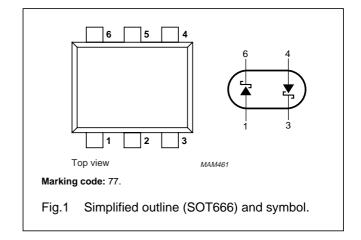
DESCRIPTION

Planar Schottky barrier double diode with an integrated guard ring for stress protection.

Two separate dies encapsulated in a SOT666 ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	anode 1
2	not connected
3	cathode 2
4	anode 2
5	not connected
6	cathode 1



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode				•	•
V _R	continuous reverse voltage		_	70	V
I _F	continuous forward current		_	70 mA	
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \delta \le 0.5$	_	70	mA
I _{FSM}	non-repetitive peak forward current	t _p < 10 ms	-	100	mA
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

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Schottky barrier double diode

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CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	see Fig.2		
		I _F = 1 mA	410	mV
		I _F = 10 mA	750	mV
		I _F = 15 mA	1	V
I _R	reverse current	V _R = 50 V; note 1; see Fig.3	100	nA
		V _R = 70 V; note 1; see Fig.3	10	μΑ
C _d	diode capacitance	V _R = 0; f = 1 MHz; see Fig.5	2	pF

Note

1. Pulse test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	416	K/W

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Note

1. Refer to SOT666 standard mounting conditions.

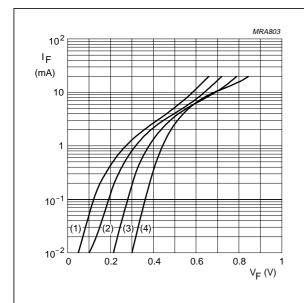
Soldering

The only recommended soldering is reflow soldering.

Schottky barrier double diode

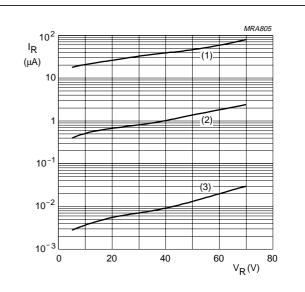
BAS70-07V

GRAPHICAL DATA



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (4) $T_{amb} = -40 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.

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(3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.

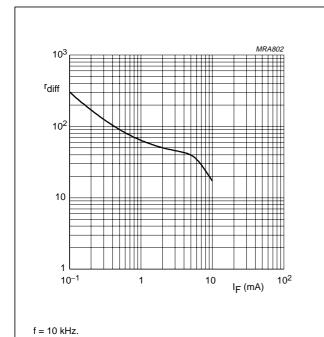


Fig.4 Differential forward resistance as a function of forward current; typical values.

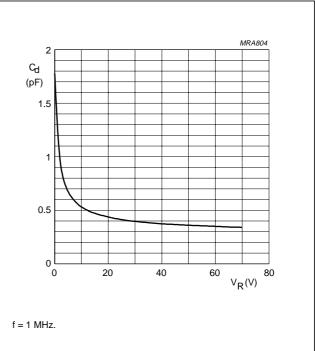


Fig.5 Diode capacitance as a function of reverse voltage; typical values.

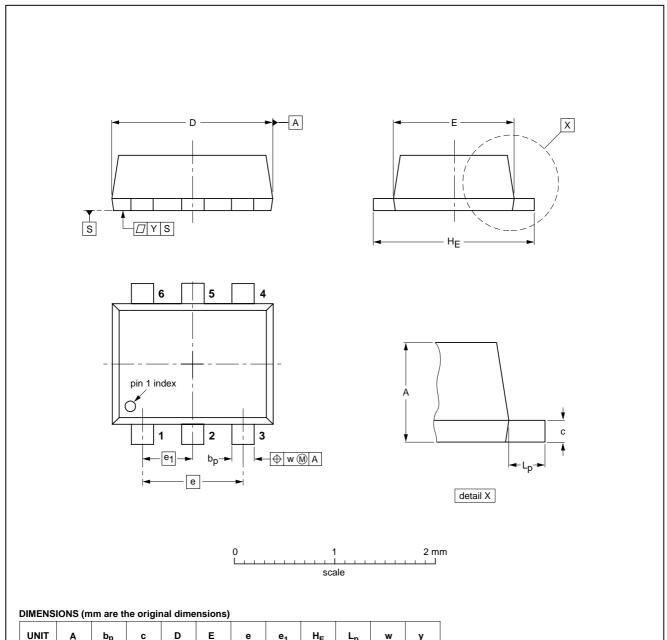
Schottky barrier double diode

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



UNIT	А	bp	С	D	E	е	e ₁	HE	Lp	w	у
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE	REFERENCES			EUROPEAN	ICCUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						-01-01-04 01-08-27

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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

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DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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